

N-Channel 80-V (D-S) MOSFET

Key Features:

- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

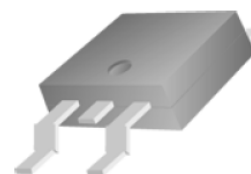
Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

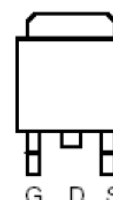
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (m Ω)	I_D (A)
80	11 @ $V_{GS} = 10V$	90 ^a
	13 @ $V_{GS} = 4.5V$	



RoHS
COMPLIANT
HALOGEN
FREE



TO-263



Top View

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ^a	$T_C = 25^\circ\text{C}$	I_D	90	A
Pulsed Drain Current ^b		I_{DM}	390	
Continuous Source Current (Diode Conduction) ^a		I_S	110	A
Power Dissipation ^a	$T_C = 25^\circ\text{C}$	P_D	300	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Case	$R_{\theta JC}$	1	

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

Electrical Characteristics

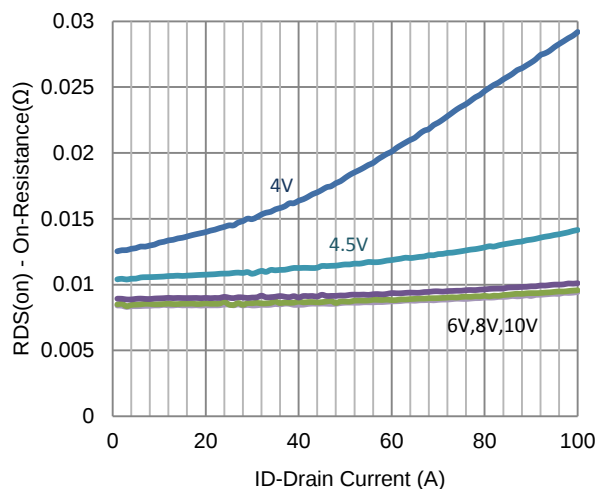
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 64 V, V_{GS} = 0 V$			1	μA
		$V_{DS} = 64 V, V_{GS} = 0 V, T_J = 55^\circ C$			25	
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 V, V_{GS} = 10 V$	120			A
Drain-Source On-Resistance	$r_{DS(on)}$	$V_{GS} = 10 V, I_D = 45 A$			11	m Ω
		$V_{GS} = 4.5 V, I_D = 44 A$			13	
Forward Transconductance	g_{fs}	$V_{DS} = 15 V, I_D = 20 A$		30		S
Diode Forward Voltage	V_{SD}	$I_S = 55 A, V_{GS} = 0 V$		0.92		V
Dynamic						
Total Gate Charge	Q_g	$V_{DS} = 40 V, V_{GS} = 4.5 V, I_D = 20 A$		60		nC
Gate-Source Charge	Q_{gs}			12		
Gate-Drain Charge	Q_{gd}			37		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 40 V, R_L = 2 \Omega, I_D = 20 A, V_{GEN} = 10 V, R_{GEN} = 6 \Omega$		19		ns
Rise Time	t_r			45		
Turn-Off Delay Time	$t_{d(off)}$			178		
Fall Time	t_f			62		
Input Capacitance	C_{iss}	$V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz$		5052		pF
Output Capacitance	C_{oss}			471		
Reverse Transfer Capacitance	C_{rss}			466		

Notes

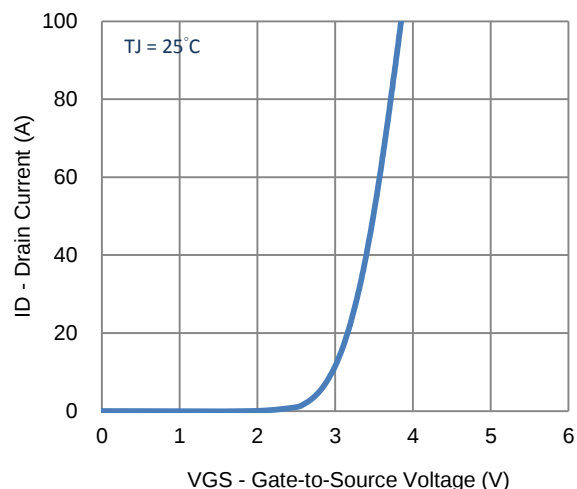
- Pulse test: $PW \leq 300 \mu s$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

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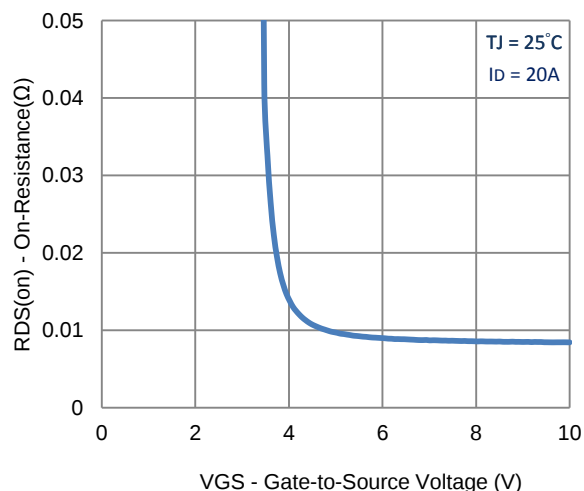
Typical Electrical Characteristics



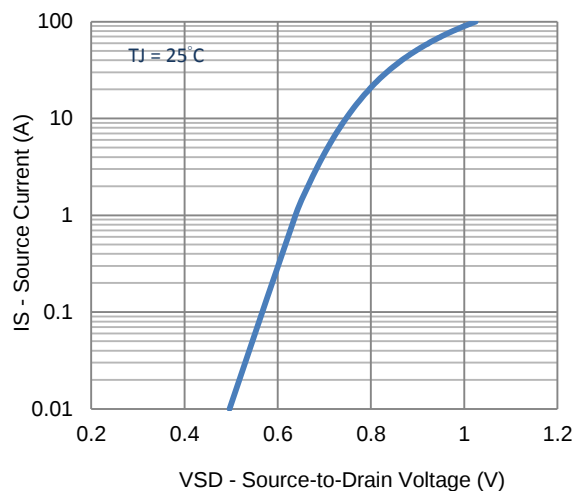
1. On-Resistance vs. Drain Current



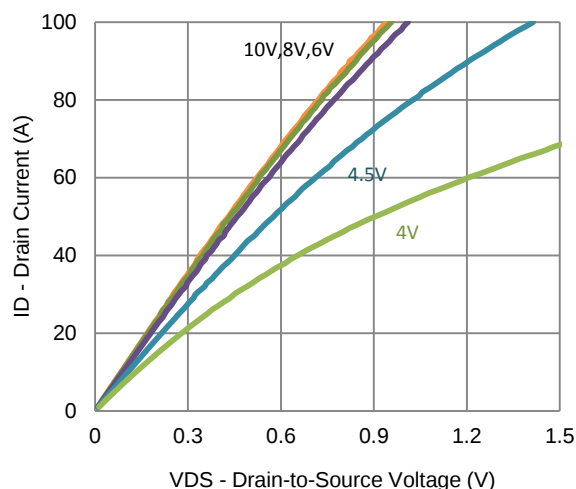
2. Transfer Characteristics



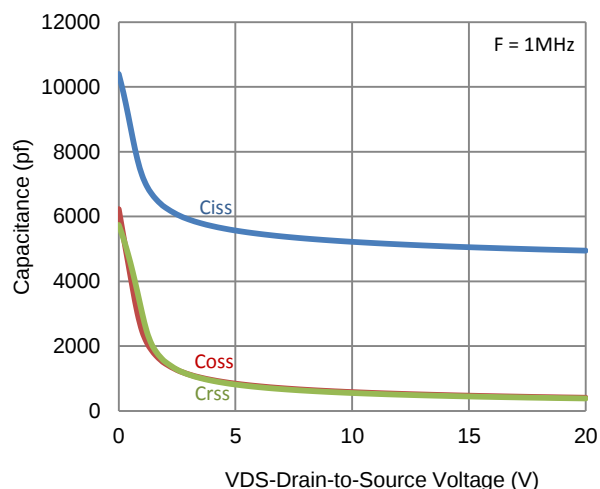
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage

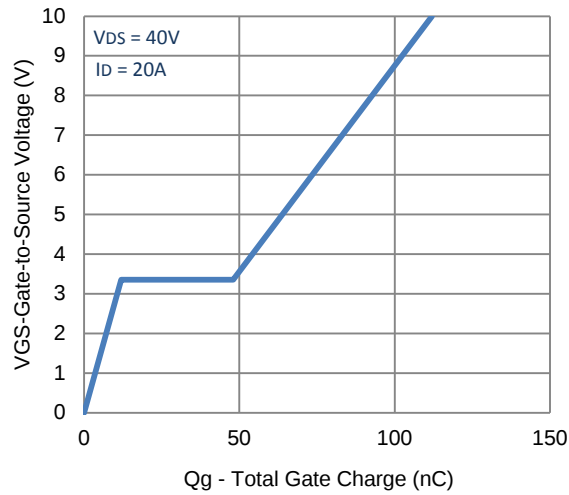


5. Output Characteristics

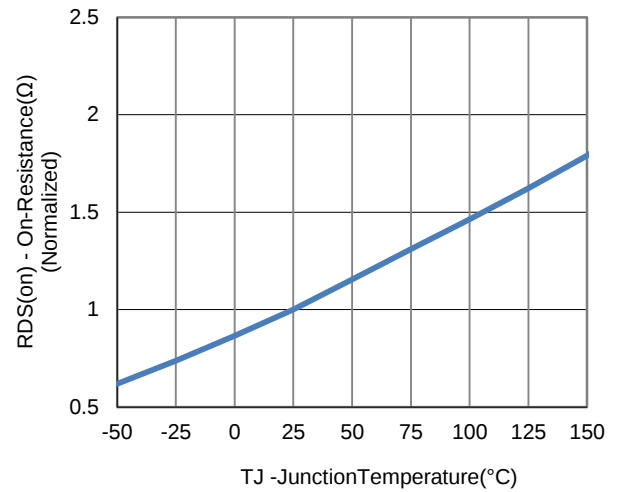


6. Capacitance

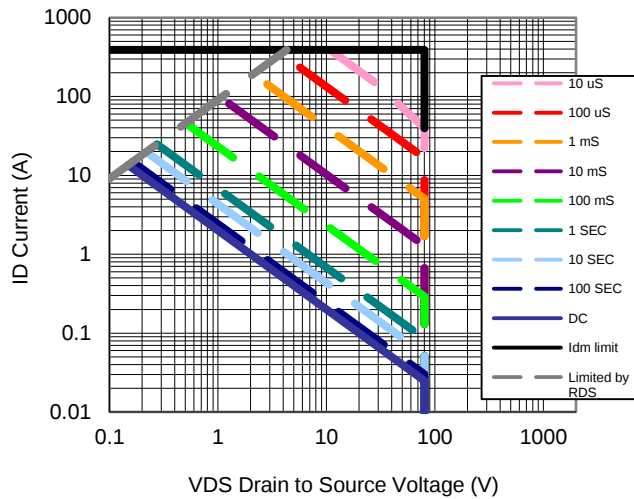
Typical Electrical Characteristics



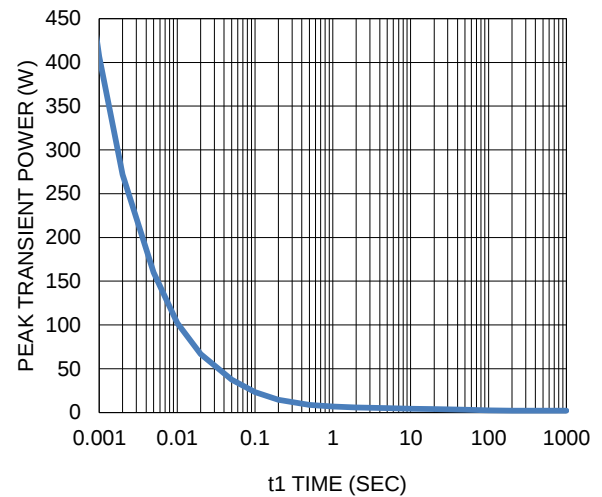
7. Gate Charge



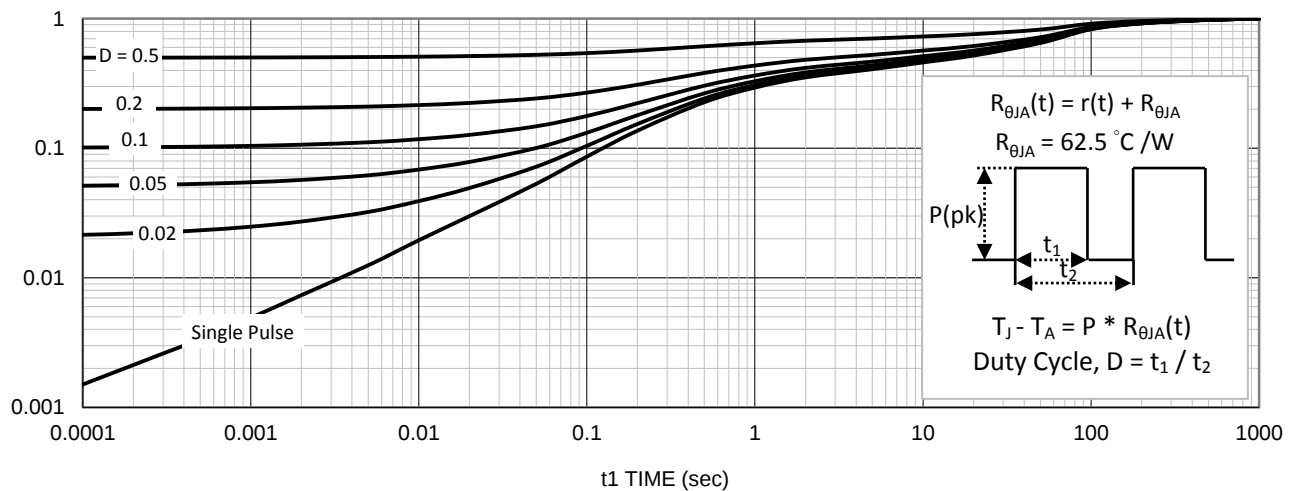
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

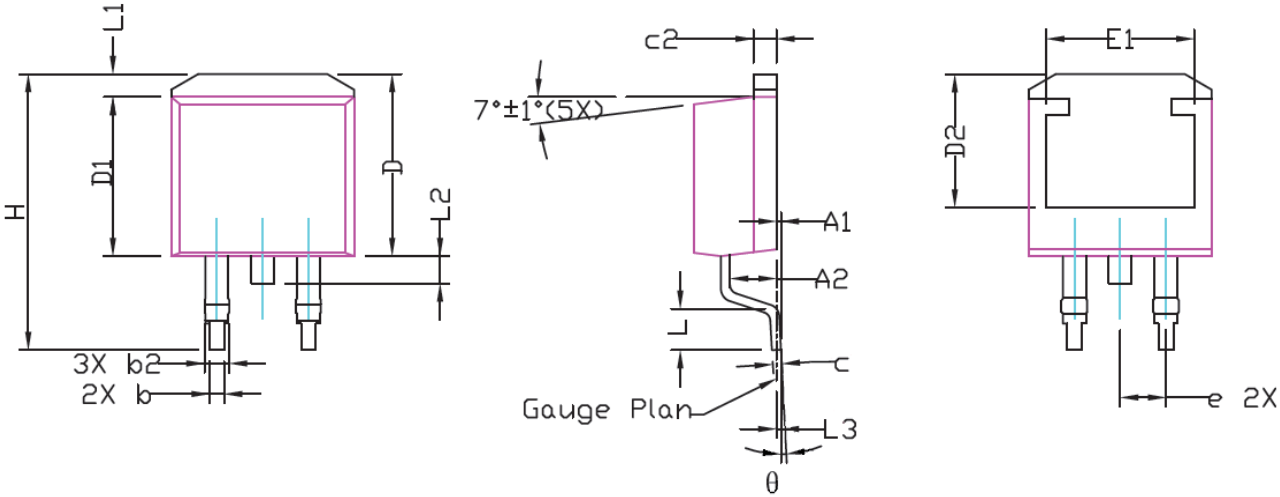


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOL	DIMENSIONAL REQMTS			INCHES REQMTS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.30	4.57	4.72	0.169	0.180	0.186
A1	0	---	0.25	0	---	0.010
A2	2.47	2.57	2.67	0.097	0.101	0.105
b	0.69	0.813	0.94	0.027	0.032	0.037
b2	1.17	1.27	1.45	0.046	0.050	0.057
c	0.48	0.50	0.60	0.019	0.020	0.024
c2	1.17	1.27	1.37	0.046	0.050	0.054
D	9.80	10.05	10.30	0.386	0.396	0.406
D1	8.64	8.78	9.65	0.340	0.346	0.380
D2	7.12	7.37	7.62	0.280	0.290	0.300
E	9.70	10.15	10.54	0.382	0.400	0.415
E1	8.00	8.20	8.40	0.315	0.323	0.331
e	2.54 BSC			0.100 BSC		
H	14.99	15.24	15.49	0.590	0.600	0.610
L	1.78	2.29	2.79	0.070	0.090	0.110
L1	1.02	1.27	1.52	0.040	0.050	0.060
L2	---	---	1.75	---	---	0.069
L3	---	0.254	---	---	0.010	---
θ	0°	---	8°	0°	---	8°